

#### IR imaging and static laser stimulation for MEMS technological evaluation and FA

Jeremie Dhennin



Optical localization techniques workshop Toulouse, 26/01/09

© Copyright 2009 - Reproduction is not allowed without authorization





- MEMS peculiarities
- When MEMS FA meet microelectronics FA techniques
- Case study #1: investigation of SOI release for optical switches – IR imaging
- Case study #2: micro switch contact detection Static laser stimulation

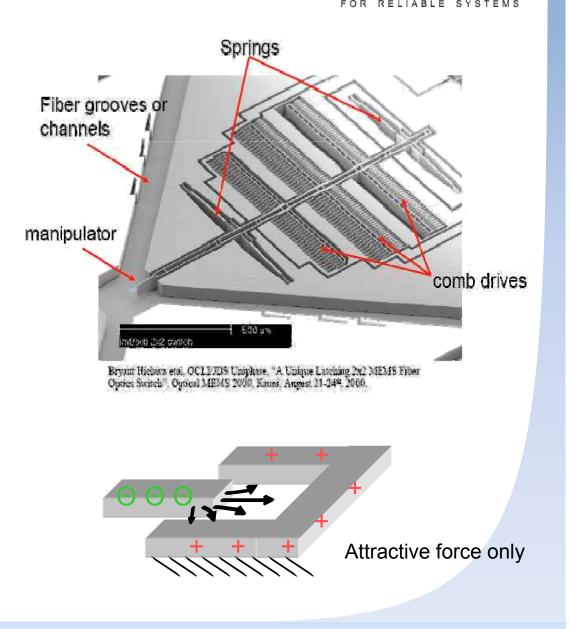


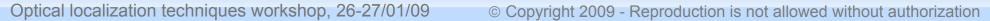
#### **MEMS** peculiarities

	I	П	Ш	IV
Categories	No movement	Movement without contacts	Movement with contacts	Sliding contacts
Examples	Chemical sensors, Inkjet printhead	Accelero, Gyro, Comb drives, Pressure sensors, Microphones	Switches, micro-mirrors, Pumps	Gears, motors
Failures	Contamination, Delamination, Electrical failure 	Class I + Deformations, Mechanical fatigue, Creep, Sticking by shock, etc.	Class II + Stiction, Impact rubbing, Micro welding	Class III + Wear, Stiction (Static friction)

#### **MEMS** peculiarities

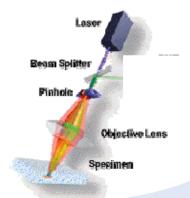
- Need dedicated techniques for FA
  - » Non intrusive
  - » Non destructive
  - » Non contact
  - » Keeping the MEMS under package
  - » Coupling electromechanico-thermal characterization





#### From microelectronics FA to MEMS FA

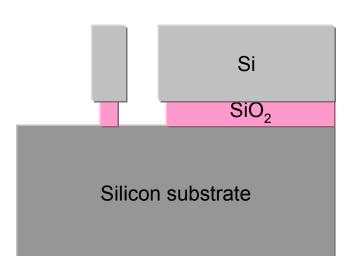
- Use of optical techniques
  - » PHEMOS 1000 from Hamamatsu
  - » 4 different objectives from 5 to 100x
  - » Resolution < 1µm enough for MEMS

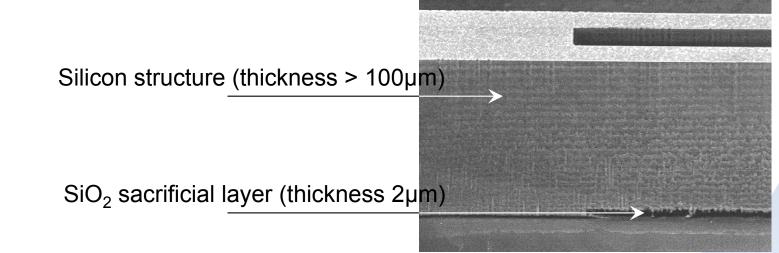




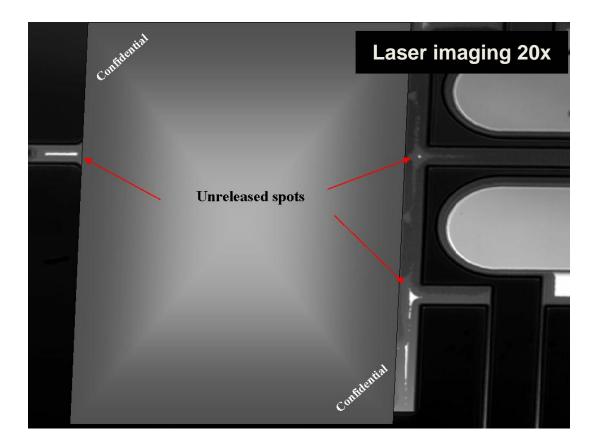


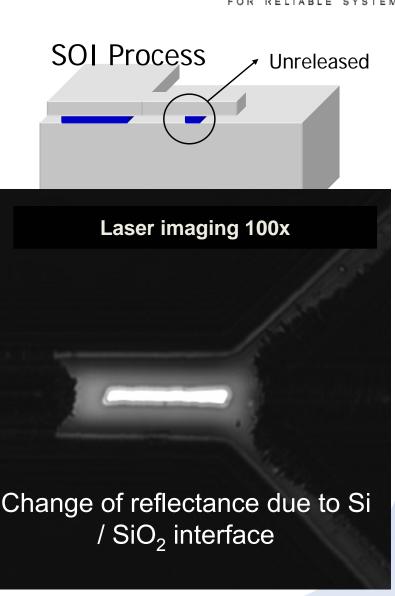
- DRIE etch of silicon layer
- Wet etching of SiO<sub>2</sub>
  - » Isotropic
  - » Release of thin parts
- Two pitfalls: under etch and over etch





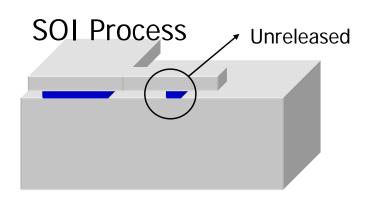
 Process optimization → etch duration

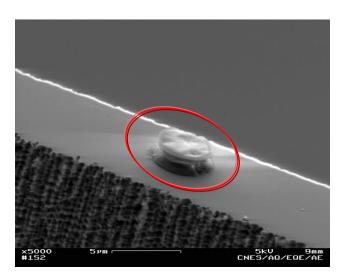




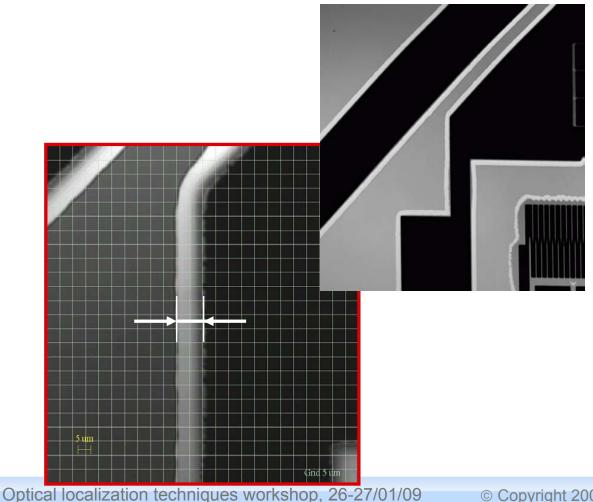
Optical localization techniques workshop, 26-27/01/09

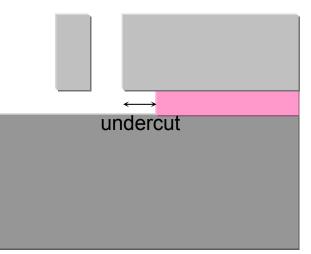
 SEM observation of SiO<sub>2</sub> traces after mobile part removal





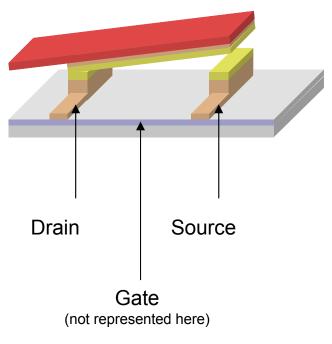
 Process optimization → undercut measurement

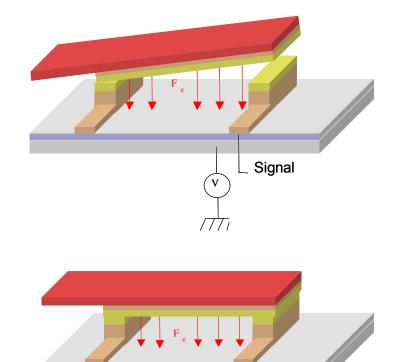






- Test structure: MEMS switch with metal / metal contact
- Electrostatic actuation





Signal

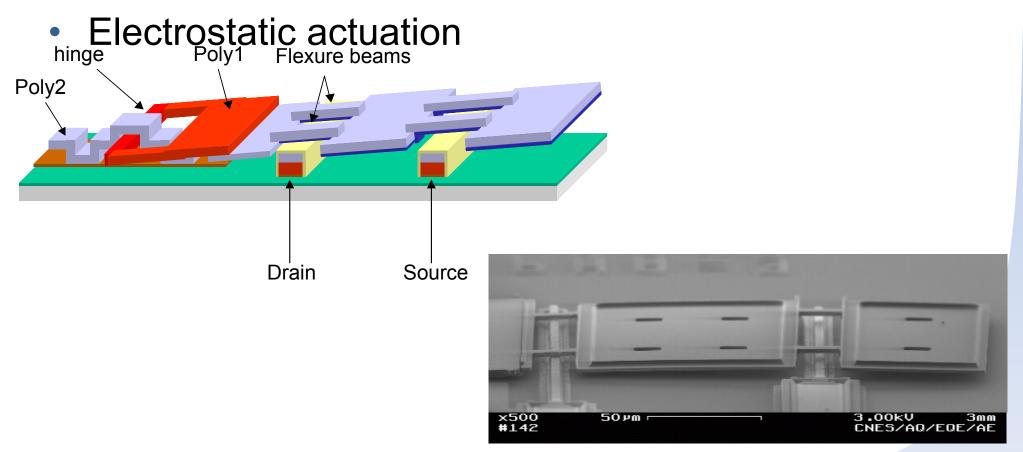
10

Out



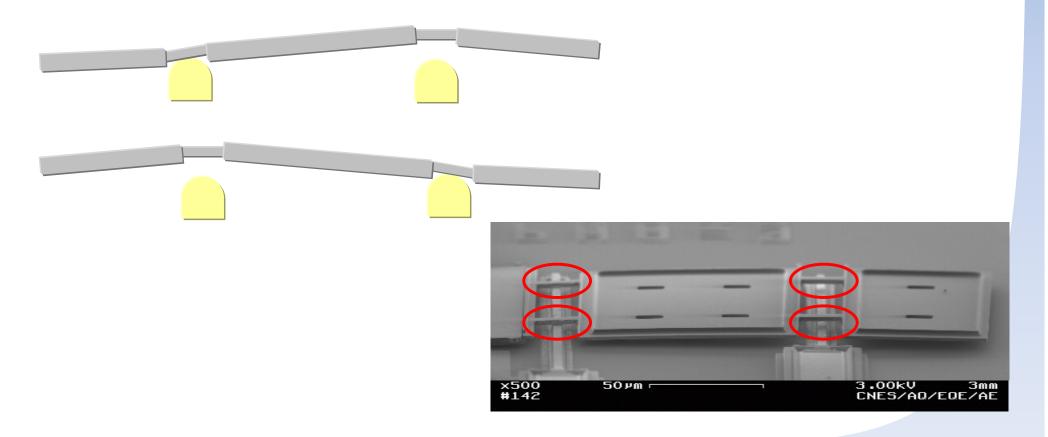
11

 Test structure: MEMS switch with metal / metal contact

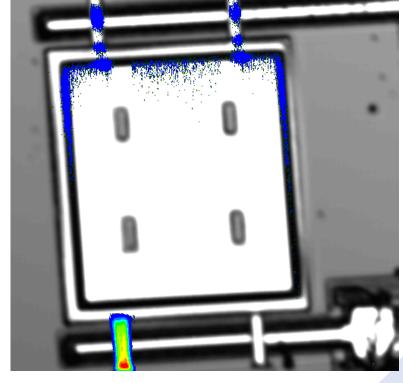




- Failure mode: Normally on
  - » Contact between the beam and the Drain/Source



- Failure mode: Normally on
  - » No biased TLS: Seebeck effect imaging
  - » Accurate localization of the poor, good and no contact zones
  - » Warping of the structure due to high stress
  - » Process issue!!



20x magnification



#### Conclusion



- Use of IR confocal microscopy techniques for MEMS FA
  - » Simple and accurate defect localization
  - » Through Silicon cap
  - » Non destructive
  - » Very helpful for reliability studies